

4A, 200V - 600V Surface Mount Ultrafast Power Rectifier

FEATURES

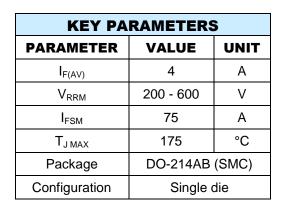
- Glass passivated junction
- Ideal for automated placement
- Built-in strain relief
- Ultrafast recovery time for high efficiency
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- High frequency rectification
- Freewheeling application
- Switching mode converters and inverters in computer, automotive and telecommunication.

MECHANICAL DATA

- Case: DO-214AB (SMC)
- Molding compound meets UL 94V-0 flammability rating
- Part no. with suffix "H" means AEC-Q101 qualified
- Packing code with suffix "G" means green compound (halogen-free)
- Moisture sensitivity level: level 1, per J-STD-020
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.25 g (approximately)







DO-214AB (SMC)

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)							
PARAMETER	SYMBOL	MUR420S	MUR440S	MUR460S	UNIT		
Marking code on the device		MUR420S	MUR440S	MUR460S			
Repetitive peak reverse voltage	V_{RRM}	200	400	600	V		
Reverse voltage, total rms value	$V_{R(RMS)}$	140	280	420	V		
Maximum DC blocking voltage	V_{DC}	200	400	600	V		
Forward current	I _{F(AV)}		4		Α		
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	75			А		
Junction temperature	T _J	- 55 to +175			°C		
Storage temperature	T _{STG}		- 55 to +175		°C		

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THERMAL PERFORMANCE						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-ambient thermal resistance per diode	$R_{\Theta JA}$	45	°C/W			
Junction-to-case thermal resistance per diode	R _{eJC}	8.5	°C/W			

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	PARAMETER			TYP.	MAX.	UNIT	
	MUR420S		V _F	-	0.875	V	
Forward voltage per diode (1)	MUR440S MUR460S	$I_F = 4A, T_J = 25^{\circ}C$		-	1.250	V	
Forward voltage per diode	MUR420S			-	0.710	V	
	MUR440S MUR460S		V_{F}	-	1.050	V	
	MUR420S		I _R	-	5	μA	
Reverse current @ rated V _R	MUR440S MUR460S	T _J = 25°C		-	10	μA	
per diode ⁽²⁾	MUR420S		I _R	-	150	μΑ	
	MUR440S MUR460S	T _J = 150°C		-	250	μΑ	
Junction capacitance		1 MHz, V _R =4.0V	CJ	65	-	pF	
	MUR420S	I _F =0.5A , I _R =1.0A	t _{rr}	-	25	ns	
Reverse recovery time	MUR440S MUR460S	I _{RR} =0.25A		-	50	ns	

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms

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RDERING INFORMATION							
PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	PACKAGE	PACKING		
	Н	R7	G	SMC	850 / 7" Plastic reel		
		R6		SMC	3,000 / 13" Paper reel		
MUR4xxS (Note 1)		M6		SMC	3,000 / 13" Plastic reel		
(Note 1)		V7		Matrix SMC	850 / 7" Plastic reel		
		V6		Matrix SMC	3,000 / 13" Plastic reel		

Note:

^{1. &}quot;xx" defines voltage from 50V (MUR42S) to 600V (MUR460S)

EXAMPLE						
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION	
MUR420SHR7G	MUR420S	Н	R7	G	AEC-Q101 qualified Green compound	



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Forward Current Derating Curve

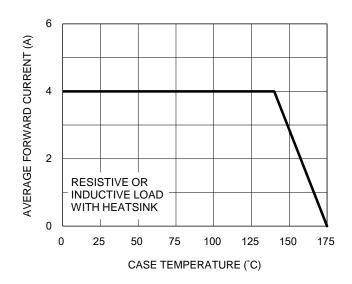


Fig.2 Typical Junction Capacitance

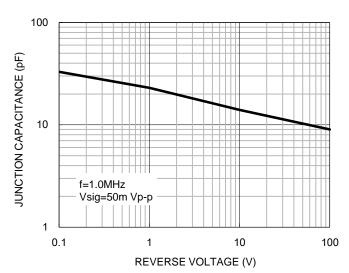


Fig.3 Typical Reverse Characteristics

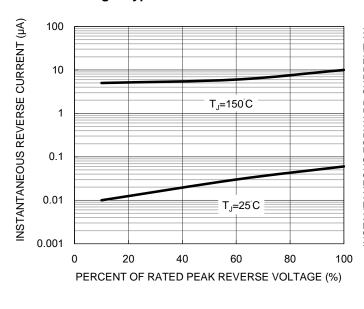
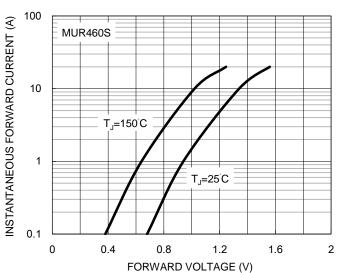


Fig.4 Typical Forward Characteristics

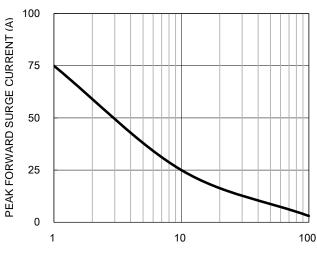




CHARACTERISTICS CURVES

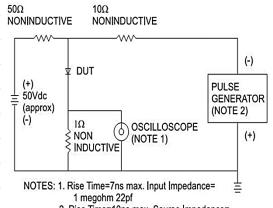
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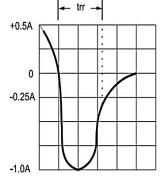
Fig.5 Maximum Non-repetitive Forward Surge Current



NUMBER OF CYCLES AT 60 Hz

Fig.6 Reverse Recovery Time Characteristic And Test Circuit Diagram



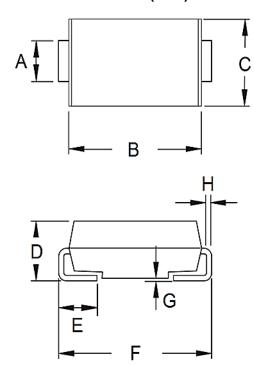


Rise Time=10ns max. Sourse Impedance=
50 ohms



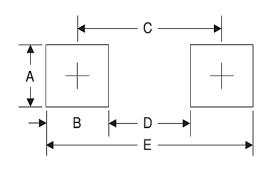
PACKAGE OUTLINE DIMENSIONS

DO-214AB (SMC)



DIM.	Unit	(mm)	Unit (inch)		
DIIVI.	Min.	Max.	Min.	Max.	
Α	2.90	3.20	0.114	0.126	
В	6.60	7.11	0.260	0.280	
С	5.59	6.22	0.220	0.245	
D	2.00	2.62	0.079	0.103	
E	1.00	1.60	0.039	0.063	
F	7.75	8.13	0.305	0.320	
G	0.10	0.20	0.004	0.008	
Н	0.15	0.31	0.006	0.012	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
А	3.30	0.130
В	2.50	0.098
С	6.80	0.268
D	4.40	0.173
Е	9.40	0.370

MARKING DIAGRAM



P/N =Marking Code

G =Green Compound

YW =Date Code F =Factory Code



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